

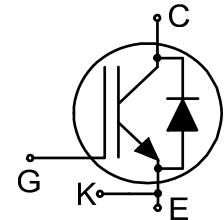
High speed switching series third generation IGBT

Low switching losses IGBT in Highspeed3 technology copacked with soft, fast recovery full current rated anti-parallel Emitter Controlled diode

Features:

High speed H3 technology offers:

- Ultra-low loss switching losses thanks to Kelvin emitter pin package in combination with High speed H3 technology
- High efficiency in hard switching and resonant topologies
- 10µsec short circuit withstand time at $T_{vj}=175^{\circ}\text{C}$
- Easy paralleling capability due to positive temperature coefficient in $V_{CE(sat)}$
- Low EMI
- Low Gate Charge Q_G
- Very soft, fast recovery full current anti-parallel diode
- Maximum junction temperature 175°C
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models:
<http://www.infineon.com/igbt/>



Applications:

- Industrial UPS
- Charger
- Energy Storage
- Three-level Solar String Inverter

Product Validation:

Qualified for industrial applications according to the relevant tests of JEDEC47/20/22



Key Performance and Package Parameters

Type	V_{CE}	I_C	$V_{CEsat}, T_{vj}=25^{\circ}\text{C}$	T_{vjmax}	Marking	Package
IKY50N120CH3	1200V	50A	2V	175°C	K50MCH3	PG-TO247-4-2

Table of Contents

Description	1
Table of Contents	2
Maximum Ratings	3
Thermal Resistance	3
Electrical Characteristics	4
Electrical Characteristics Diagrams	6
Package Drawing	13
Testing Conditions	14
Revision History	15
Disclaimer	16